ABSTRACT OF THE DISCLOSURE

The invention comprises FLASH memory and methods of forming flash memory. In one implementation, a line of floating gates is formed over a semiconductor substrate. The semiconductor substrate is etched to form a series of spaced trenches therein in a line adjacent and along at least a portion of the line of floating gates. At least one conductivity enhancing impurity implant is conducted into the semiconductor substrate at an angle away from normal to a general orientation of the semiconductor substrate to implant at least along sidewalls of the trenches and between the trenches, and a continuous line of source active area is formed within the semiconductor substrate along at least a portion of the line of floating gates. In another implementation, a line of floating gates is formed over a semiconductor substrate. An alternating series of trench isolation regions and active area regions are provided in the semiconductor substrate in a line adjacent and along at least a portion of the line of floating gates. The series of active areas define discrete transistor source areas separated by trench isolation regions. A conductive line is formed over the discrete transistor source areas and trench isolation regions separating same adjacent and along at least a portion of the line of floating gates. The conductive line electrically interconnects the discrete transistor source areas. Source forming conductivity enhancing impurity is provided into the discrete transistor source areas. Other implementations are contemplated.